Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel emitter-collector diode in a SOT54 (TO-92) plastic package.

2. Features and benefits

- · High typical DC current gain
- Fast switching
- · High voltage capability
- Integrated anti-parallel E-C diode

3. Applications

- Compact fluorescent lamps (CFL)
- · Low power electronic lighting ballasts
- · Off-line self-oscillating power supplies (SOPS) for battery charging

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Val	lues		Unit
Absolute	Absolute maximum rating						
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	700			V	
I _c	collector current	DC	1.5		Α		
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>		2	2.1		W
Symbol	Parameter Conditions			Min	Тур	Max	Unit
Static ch	Static characteristics						
h _{FE}	DC current gain	$I_{C} = 0.5 \text{ A}; V_{CE} = 2 \text{ V}; T_{j} = 25 \text{ °C}$		8	17	25	

NPN power transistor with integrated diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	С	collector]	
3	E	emitter	(1 (1) 3 2 1 TO-92 (SOT54)	B E E sym131

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PHD13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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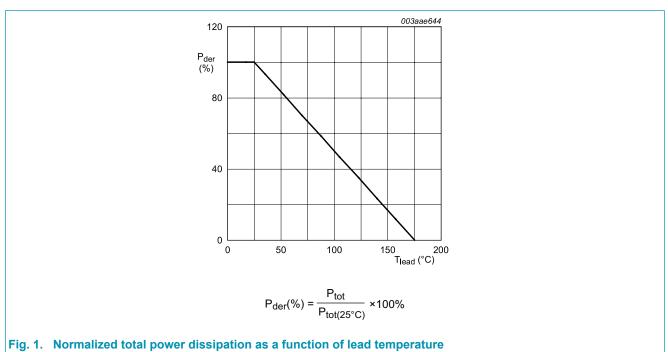
7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	700	V
V_{CBO}	collector-base voltage	I _E = 0 A	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	400	V
Ic	collector current	DC	1.5	А
I _{CM}	peak collector current		3	А
I _B	base current	DC	0.75	А
I _{BM}	peak base current		1.5	А
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	2.1	W
T _{stg}	storage temperature		-65 to 150	°C
T _j	junction temperature		150	°C
V _{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	9	V

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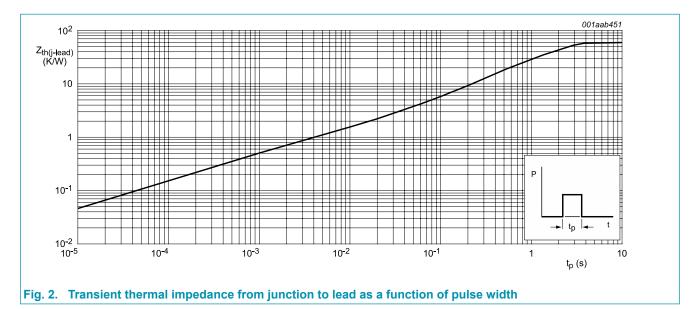


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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	Fig. 2	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance in free air; printed-circuit board mounted; lead length = 4 mm ambient		-	150	-	K/W



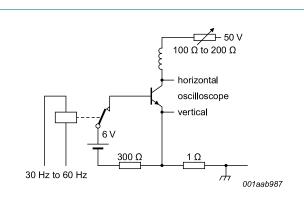
NPN power transistor with integrated diode

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		'		,	
I _{CES}	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 700 V	-	-	1	mA
	current	V _{BE} = 0 V; V _{CE} = 700 V; T _j =100°C	-	-	5	mA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{lead} = 25^{\circ}\text{C}$	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	V _{EB} = 9 V; I _C = 0 A; T _{lead} = 25°C	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25^{\circ}\text{C}; \underline{\text{Fig. 3}}; \underline{\text{Fig. 4}}$	400	-	-	V
V _{CEsat}	collector-emitter	$I_{\rm C} = 0.5 \text{A}; I_{\rm B} = 0.1 \text{A}; T_{\rm lead} = 25 ^{\circ}\text{C}$	-	-	0.5	V
	saturation voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25°C	-	-	1	V
		I _C = 1.5 A; I _B = 0.5 A; T _{lead} = 25°C	-	-	1.5	V
V_{BEsat}	base-emitter saturation voltage	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25°C	-	-	1	V
		I _C = 1 A; I _B = 0.25 A; T _{lead} = 25°C	-	-	1.2	V
V _F	forward voltage	I _F = 0.5 A; T _j = 25°C	-	-	1.5	V
h _{FE}	DC current gain	I _C = 0.5 A; V _{CE} = 2 V; T _j = 25°C	8	17	25	
		I _C = 1 A; V _{CE} = 2 V; T _j = 25°C	5	9	15	
Dynamic	characteristics					
t _{on}	turn-on time	I_C = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_L = 75 Ω ; T_{Iead} = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	1	μs
t _s	storage time	I_{C} = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_{L} = 75 Ω ; T_{lead} = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	4	μs
		I_C = 1 A; I_{Bon} = 0.2 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.8	-	μs
t _f	fall time	I_{C} = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_{L} = 75 Ω ; T_{lead} = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	0.7	μs
		I_{C} = 0.5 A; I_{Bon} = 0.1 A; V_{BB} = -5 V; L_{B} = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.1	-	μs

NPN power transistor with integrated diode



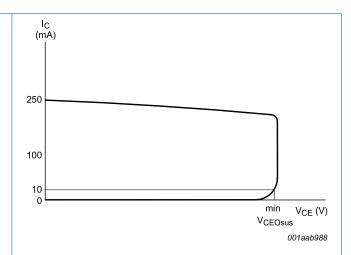
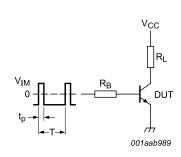


Fig. 3. Test circuit for collector-emitter sustaining voltage

Fig. 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



 V_{IM} = -6 V to +8 V; V_{CC} = 250 V; t_{p} = 20 μs ; δ = t_{p}/T = 0.01.

 R_{B} and R_{L} calculated from I_{Con} and I_{Bon} requirements

Fig. 5. Test circuit for resistive load switching

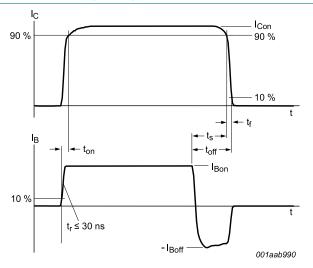
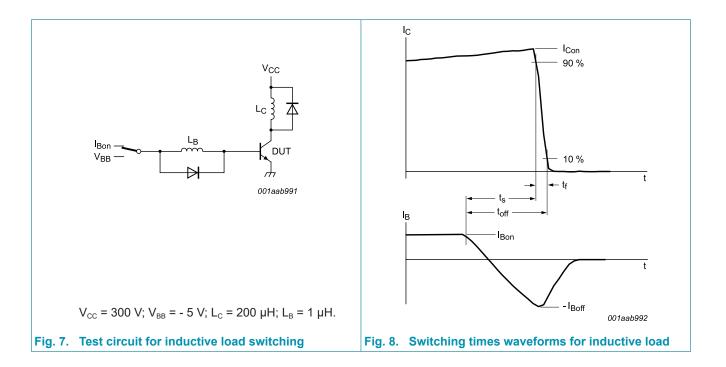


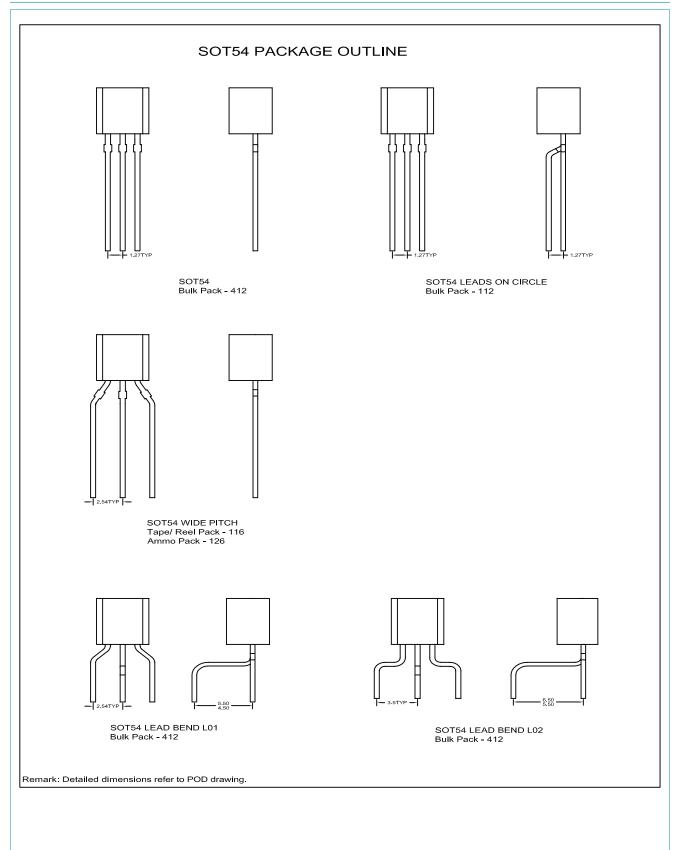
Fig. 6. Switching times waveforms for resistive load

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10. Package outline



NPN power transistor with integrated diode

11. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PHD13003C v.2	20180224	Product data sheet	-	PHD13003C v.1	
Modifications: Change from NXP version to WeEn version					
PHD13003C v.1	20100729	Product data sheet	-	-	

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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